

Title (en)

BOTTOM GATE TYPE THIN FILM TRANSISTOR, ITS MANUFACTURING METHOD AND LIQUID CRYSTAL DISPLAY DEVICE USING THE SAME

Title (de)

DÜNNFILMTRANSISTOR MIT UNTENLIEGENDEM GATE, DESSEN HERSTELLUNGSVERFAHREN UND FLÜSSIGKRISTALLANZEIGEGERÄT

Title (fr)

TRANSISTOR A COUCHES MINCES DE TYPE GRILLE INFÉRIEURE, SON PROCÉDE DE FABRICATION ET DISPOSITIF D'AFFICHAGE A CRISTAUX LIQUIDES UTILISANT CE TRANSISTOR

Publication

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Application

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Abstract (en)

[origin: WO0201603A2] The object of the invention is to provide a bottom gate type thin film transistor and a manufacturing method of it, which can reduce a burden of TFT manufacturing process and thereby a less manufacturing cost is required. A bottom gate type thin film transistor is provided, in which a base layer (1), a gate electrode (2), a gate isolation film (3), and source and drain electrodes (4, 5) are located in this order. The transistor comprises a semiconductor channel layer (6) which is in contact with a portion of the gate isolation film exposed between the source and drain electrodes (4, 5) while being in contact with respective inter-opposite ends of the source and drain electrodes (4,5) and being formed in association with the gate electrode (2). The channel layer (6) is bridged from one of the inter-opposite ends to the other on the upper face side of the source and drain electrodes (4, 5). Contact portions (6c) of the channel layer (6) with the source and drain electrodes (4, 5) form ohmic contact surface layers.

IPC 1-7

H01L 21/36

IPC 8 full level

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